NJD35N04G, NJVNJD35N04G, NJVNJD35N04T4G

NPN Darlington Power Transistor

This high voltage power Darlington has been specifically designed for inductive applications such as Electronic Ignition, Switching Regulators and Motor Control.

Features

- Exceptional Safe Operating Area
- High V_{CE}; High Current Gain
- NJV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q101 Qualified and PPAP Capable
- These are Pb−Free Devices*

Benefits

- Reliable Performance at Higher Powers
- Designed for Inductive Loads
- Very Low Current Requirements

Applications

- Internal Combustion Engine Ignition Control
- Switching Regulators
- Motor Controls
- Light Ballast
- Photo Flash

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector−Emitter Sustaining Voltage	V_{CEO}	350	Vdc
Collector−Base Breakdown Voltage	V_{CBO}	700	Vdc
Collector−Emitter Breakdown Voltage	V_{CES}	700	Vdc
Emitter−Base Voltage	V_{EBO}	5.0	Vdc
Collector Current Continuous Peak	 I_C I_{CM}	 4.0 8.0	Adc
Base Current	I_B	0.5	Adc
Total Power Dissipation @ T_C = 25°C Derate above 25°C	P_D	 45 0.36	 W W/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

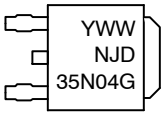
ON Semiconductor®

http://onsemi.com

DARLINGTON POWER TRANSISTORS 4 AMPERES 350 VOLTS 45 WATTS

DPAK
CASE 369C
STYLE 1

MARKING DIAGRAM



Y = Year
WW = Work Week
NJD35N04 = Device Code
G = Pb−Free Device

ORDERING INFORMATION

Device	Package	Shipping†
NJD35N04G	DPAK (Pb−Free)	75 Units / Rail
NJVNJD35N04G	DPAK (Pb−Free)	75 Units / Rail
NJD35N04T4G	DPAK (Pb−Free)	2,500 / Tape & Reel
NJVNJD35N04T4G	DPAK (Pb−Free)	2,500 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Thermal Resistance Junction−to−Case Junction−to−Ambient	 $R_{\theta JC}$ $R_{\theta JA}$	 2.78 71.4	°C/W

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector−Emitter Sustaining Voltage (I_C = 10 mA, L = 10 mH)	$V_{CEO(sus)}$	 350	 –	 –	V
Collector Cutoff Current (V_{CE} = 500 V) (I_B = 0) (V_{CE} = 500 V, T_C = 125°C)	I_{CES}	– –	– –	50 250	μA
Collector Cutoff Current (V_{CE} = 250 V) (I_B = 0) (V_{CE} = 200 V, T_C = 125°C)	I_{CEO}	– –	– –	50 250	μA
Emitter Cutoff Current (V_{BE} = 5.0 Vdc)	I_{EBO}	–	–	5.0	μA
ON CHARACTERISTICS					
Collector−Emitter Saturation Voltage (I_C = 2.0 A, I_B = 20 mA) (I_C = 2.0 A, I_B = 20 mA 125°C)	$V_{CE(sat)}$	 – –	 – –	 1.5 1.5	V
Base−Emitter Saturation Voltage (I_C = 2.0 A, I_B = 20 mA) (I_C = 2.0 A, I_B = 20 mA 125°C)	$V_{BE(sat)}$	 – –	 – –	 2.0 2.0	V
Base−Emitter On Voltage (I_C = 2.0 A, V_{CE} = 2.0 V) (I_C = 2.0 A, V_{CE} = 2.0 V, 25°C)	$V_{BE(on)}$	 – –	 – –	 2.0 2.0	V
DC Current Gain (I_C = 2.0 A, V_{CE} = 2.0 V) (I_C = 4.0 A, V_{CE} = 2.0 Vdc)	h_{FE}	 2000 300	 – –	 – –	–
DYNAMIC CHARACTERISTICS					
Current−Gain − Bandwidth Product (I_C = 2.0 A, V_{CE} = 10 V, f = 1.0 MHz)	f_T	 90	 –	 –	MHz
Output Capacitance (V_{CB} = 10 V, I_E = 0, f = 0.1 MHz)	C_{ob}	 –	 60	 –	pF
SWITCHING CHARACTERISTICS					
V_{CC} = 12 V, V_{clamp} = 250 V, L = 4 mH I_C = 2 A, I_{B1} = 20 mA, I_{B2} = −20 mA	t_s t_f	– –	18 0.8	– –	μSec

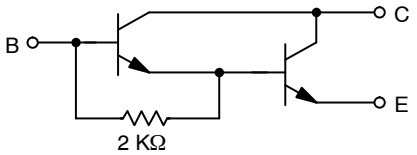


Figure 1. Darlington Circuit Schematic

TYPICAL CHARACTERISTICS

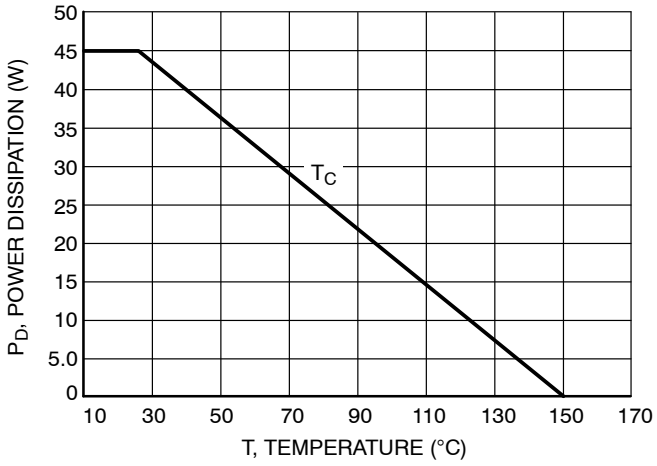


Figure 2. Power Derating

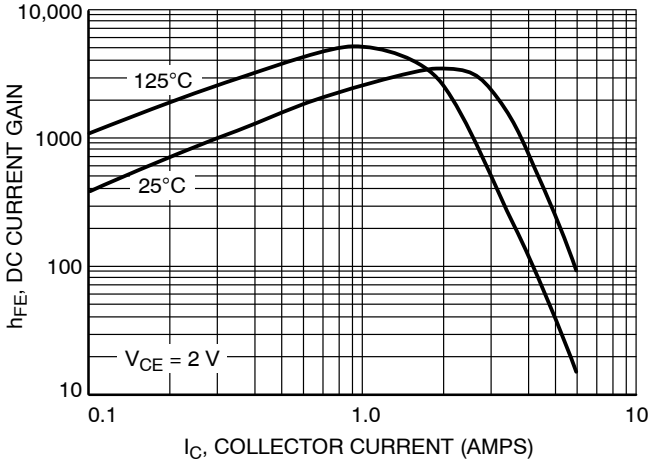


Figure 3. DC Current Gain

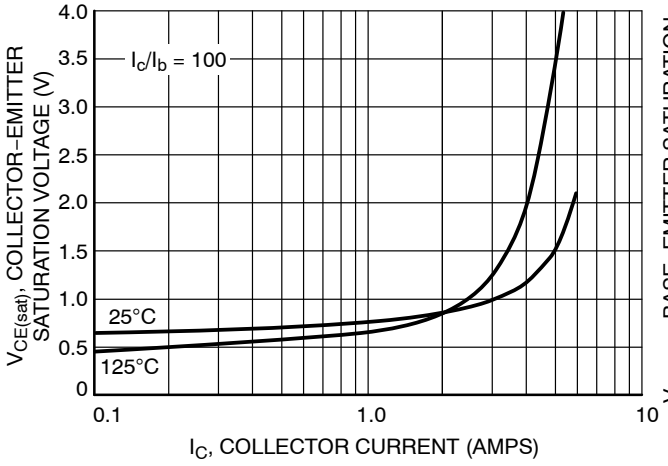


Figure 4. Collector−Emitter Saturation Voltage

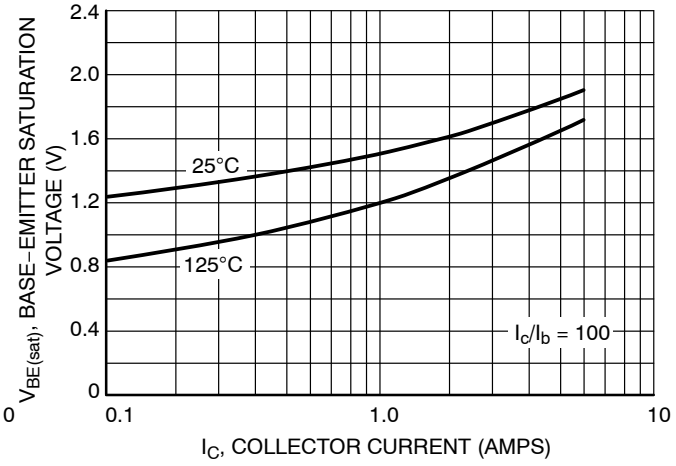


Figure 5. Base−Emitter Saturation Voltage

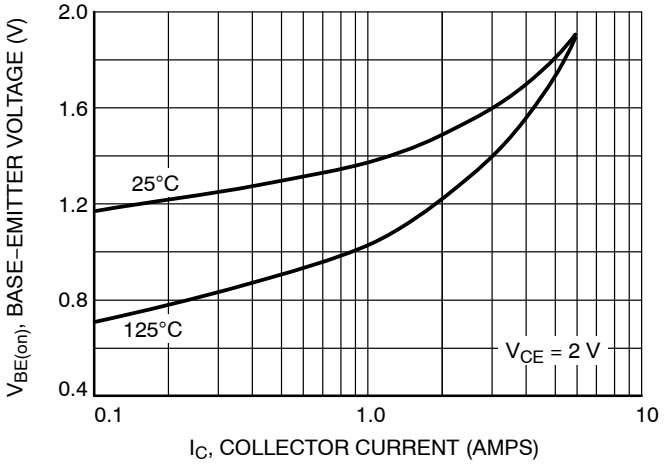


Figure 6. Base−Emitter Voltage

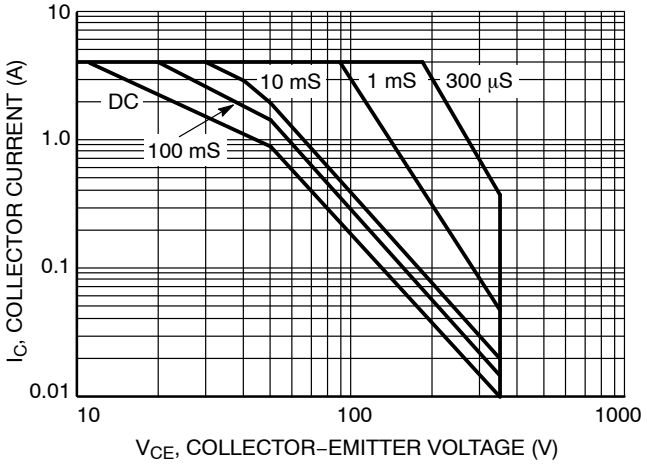
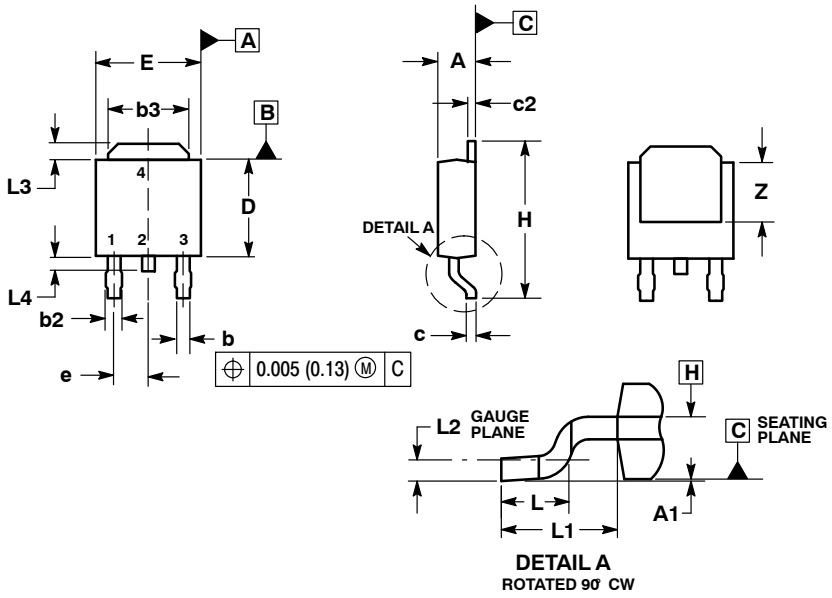


Figure 7. Forward Bias Safe Operating Area (FBSOA)

PACKAGE DIMENSIONS

DPAK
CASE 369C−01
ISSUE D

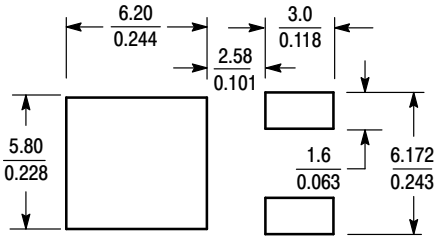


NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCHES.
3. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS b3, L3 and Z.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.
5. DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
6. DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.086	0.094	2.18	2.38
A1	0.000	0.005	0.00	0.13
b	0.025	0.035	0.63	0.89
b2	0.030	0.045	0.76	1.14
b3	0.180	0.215	4.57	5.46
c	0.018	0.024	0.46	0.61
c2	0.018	0.024	0.46	0.61
D	0.235	0.245	5.97	6.22
E	0.250	0.265	6.35	6.73
e	0.090 BSC		2.29 BSC	
H	0.370	0.410	9.40	10.41
L	0.055	0.070	1.40	1.78
L1	0.108 REF		2.74 REF	
L2	0.020 BSC		0.51 BSC	
L3	0.035	0.050	0.89	1.27
L4	−−−	0.040	−−−	1.01
Z	0.155	−−−	3.93	−−−

STYLE 1:
PIN 1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

SOLDERING FOOTPRINT*



SCALE 3:1 $\left(\frac{\text{mm}}{\text{inches}}\right)$

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
P.O. Box 5163, Denver, Colorado 80217 USA
Phone: 303−675−2175 or 800−344−3860 Toll Free USA/Canada
Fax: 303−675−2176 or 800−344−3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800−282−9855 Toll Free USA/Canada
Europe, Middle East and Africa Technical Support:
Phone: 421 33 790 2910
Japan Customer Focus Center
Phone: 81−3−5817−1050

ON Semiconductor Website: **www.onsemi.com**

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative

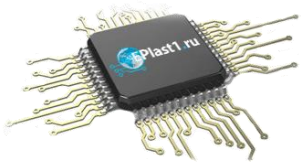
Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits,General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

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